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Journal of Materials Chemistry

Facile Chemical Photopatterning of POSS Derivatives Toward 'Green' Semiconductor Manufacturing

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Supplementary Information

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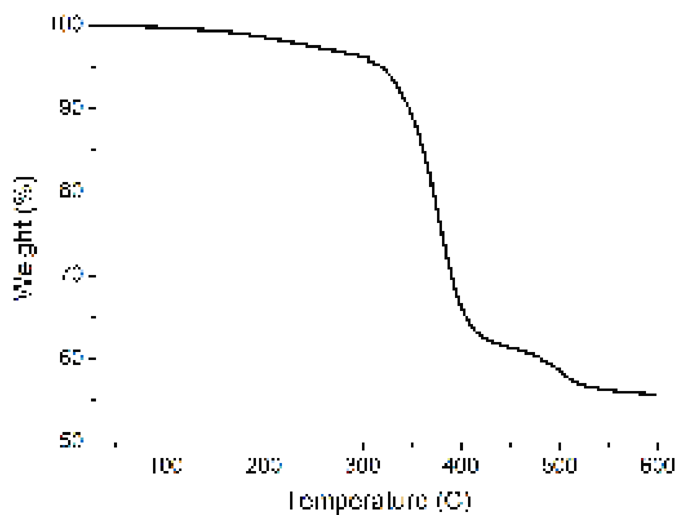

Fig. S1 TGA plot of POSS **1b** exposed to air atmosphere.

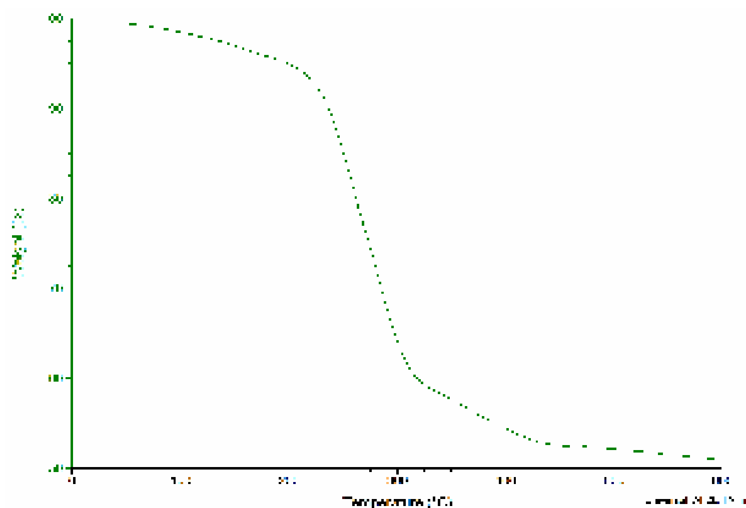

Fig. S2 TGA plot of POSS **1a** exposed to air atmosphere.

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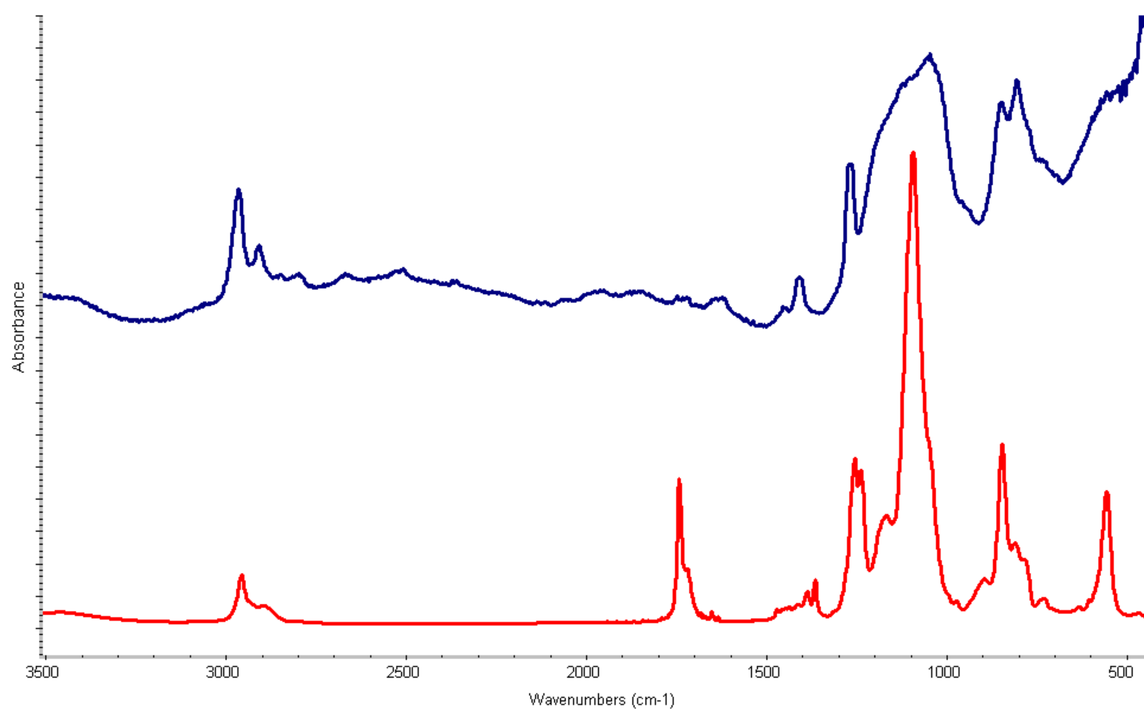

Fig. S3 FT-IR spectra of POSS **1b** (lower) and of POSS 1b cured at 300 °C for 1 h (upper).

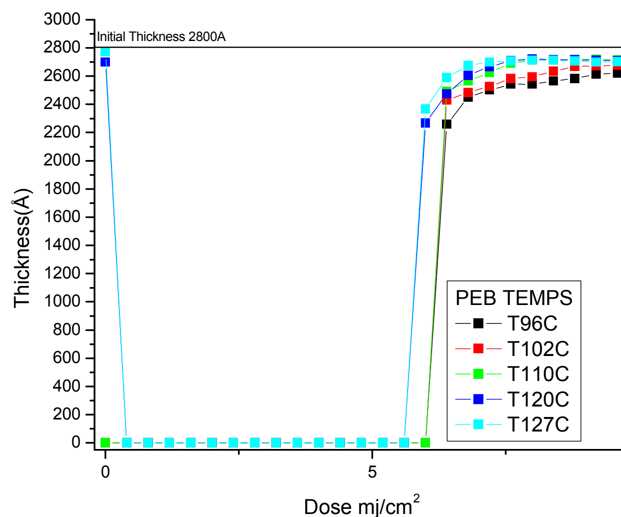

Fig. S4 Contrast curves for POSS **1a** formulated with 4 parts triphenylsulfonium nonaflate after performing a post-applied bake temperature of 90 °C and using a range of post-exposure bake temperatures (96-127 °C).

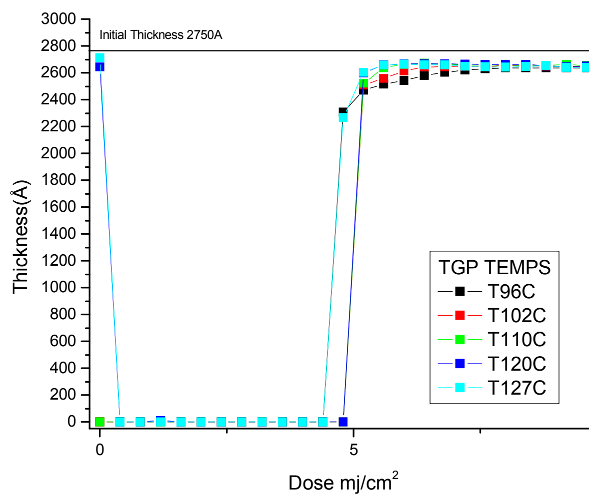

Fig. S5 Contrast curves for POSS **1b** formulated with 4 parts triphenylsulfonium nonaflate after performing a post-applied bake temperature of 90 °C and using a range of post-exposure bake temperatures (96-127 °C).